

Switching Diode

1SS400

●Applications

High speed switching

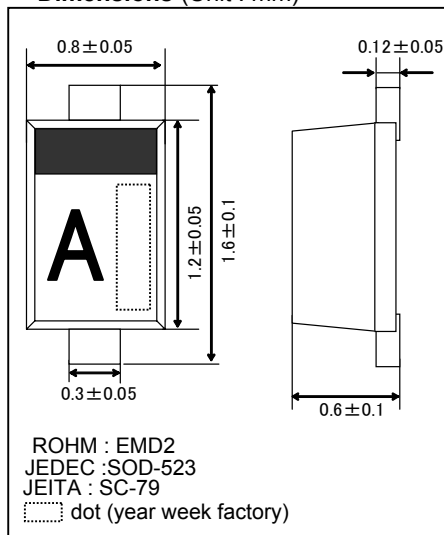
●Features

- 1) Ultra small mold type. (EMD2)
- 2) High reliability

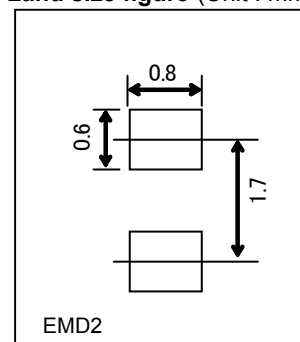
●Construction

Silicon epitaxial planar

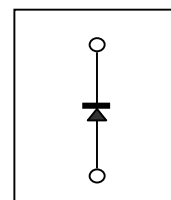
●Dimensions (Unit : mm)



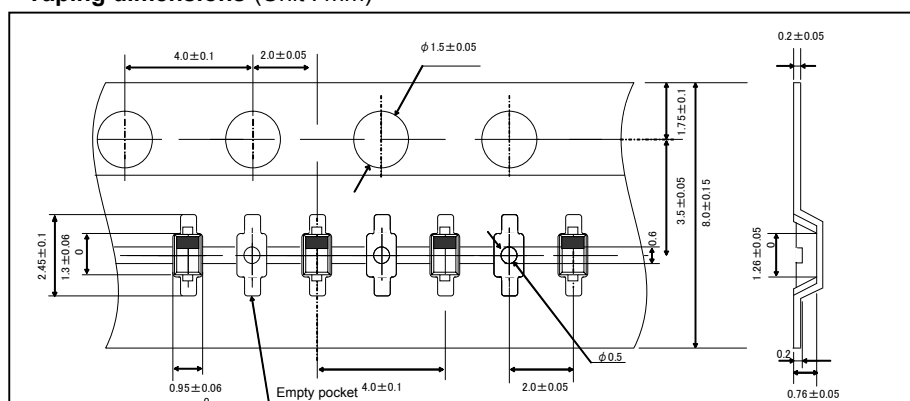
●Land size figure (Unit : mm)



● Structure



●Taping dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive)	V_{RM}	90	V
Reverse voltage (DC)	V_R	80	V
Forward voltage(repetitive peak)	I_{FM}	225	mA
Average rectified forward current	I_o	100	mA
Surge current(t=1s)	I_{surge}	500	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	1.2	V	$I_F=100\text{mA}$
Reverse current	I_R	-	-	0.1	μA	$V_R=80\text{V}$
Capacitance between terminals	C_t	-	-	3	pF	$V_R=0.5\text{V}$, $f=1\text{MHz}$
Reverse recovery time	t_{rr}	-	-	4	ns	$V_R=6\text{V}$, $I_F=10\text{mA}$, $R_L=100\Omega$

